

Semiclassical Poisson and Self-Consistent Poisson-Schrodinger Solvers in QCAD

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Andrew Salinger, Richard Muller



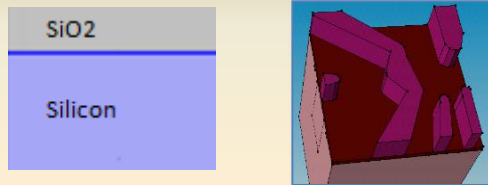
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Outline

Poisson Solver Background

$$-\nabla(\epsilon_s \nabla \phi) = q(p - n + N_D^+ - N_A^-)$$

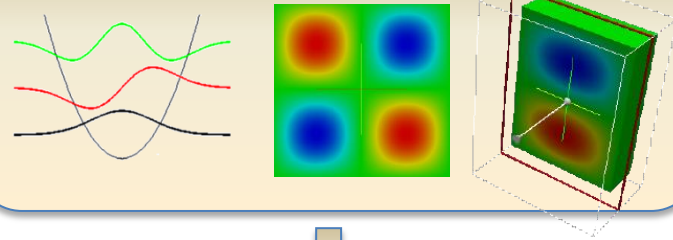
Applications of Poisson Solver



Schrodinger Solver

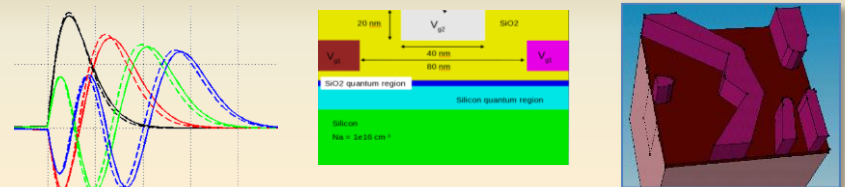
$$-\frac{\hbar^2}{2} \nabla \left(\frac{1}{m^*} \nabla \psi \right) + V\psi = E\psi$$

Applications of Schrodinger Solver



Self-Consistent Poisson-Schrodinger Solver

Applications of Self-Consistent P-S Solver



Poisson Solver – Carrier Statistics

Poisson equation in a semiconductor: $-\nabla(\epsilon_s \nabla \phi) = q(p - n + N_D^+ - N_A^-)$

$$\underbrace{p - n + N_D^+ - N_A^-}_{f(\phi)} = ?$$

Maxwell-Boltzmann (MB) statistics

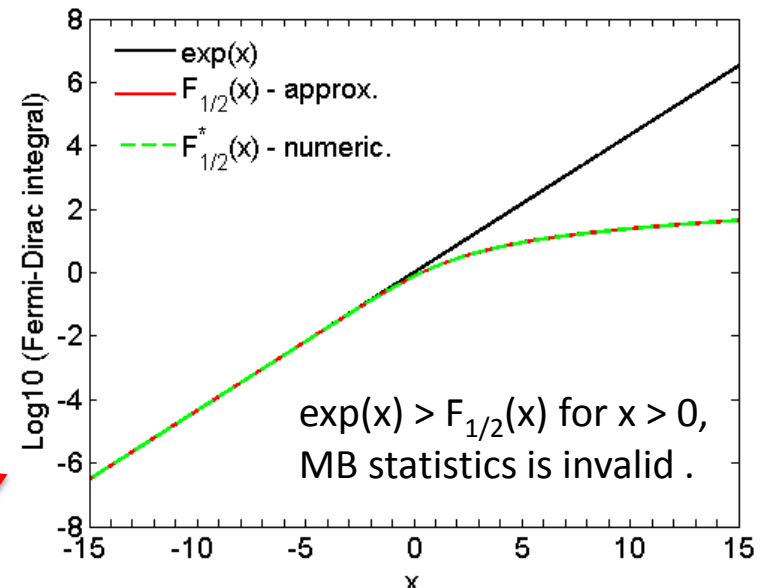
$$n = N_C \exp\left(\frac{E_F - E_C}{k_B T}\right) \quad p = N_V \exp\left(\frac{E_V - E_F}{k_B T}\right)$$

Fermi-Dirac (FD) statistics

$$n = N_C F_{1/2}\left(\frac{E_F - E_C}{k_B T}\right) \quad p = N_V F_{1/2}\left(\frac{E_V - E_F}{k_B T}\right)$$

Fermi-Dirac integral of 1/2 order

$$F_{1/2}(x) = \frac{2}{\sqrt{\pi}} \int_0^\infty \frac{\sqrt{\epsilon} d\epsilon}{1 + \exp(\epsilon - x)}$$

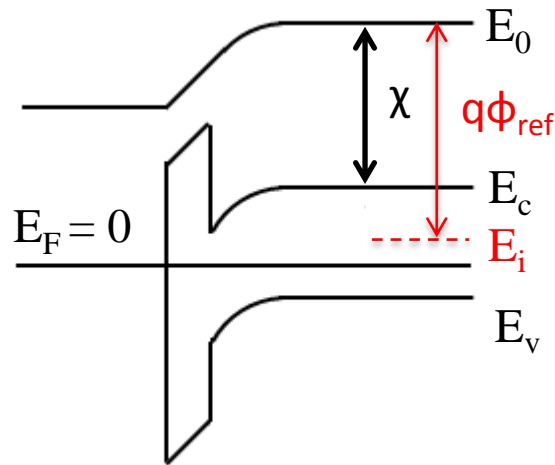


Approx. $F_{1/2}(x) = \left[e^{-x} + \frac{3\sqrt{\pi}}{4} \nu^{-3/8} \right]^{-1} \quad [1]$

$$\nu = x^4 + 50 + 33.6x \{ 1 - 0.68 \exp[-0.17(x+1)^2] \}$$

Poisson Solver – What Is Solved

Under thermal equilibrium (No current flow), $E_F = \text{const}$ through out a device, chosen to be 0 in QCAD.



$$E_c = -q(\phi - \phi_{ref}) - \chi$$

$$E_v = -q(\phi - \phi_{ref}) - \chi - E_g$$

$$n(\phi), p(\phi)$$

Heterostructure:

- E_c & E_v are **discontinuous**
- Vacuum level E_0 is **continuous**

Requirement of potential (ϕ):

- **Continuous** everywhere

Choice of potential (ϕ):

- Let $-q(\phi - \phi_{ref}) = E_0 = E_c + \chi$

Constant shift

Choice of $q\phi_{ref}$ does not change the locations and profiles of E_c and E_v w.r.t. E_F , but could lead to different numerical behavior during simulation.

Poisson Solver – Incomplete Ionization

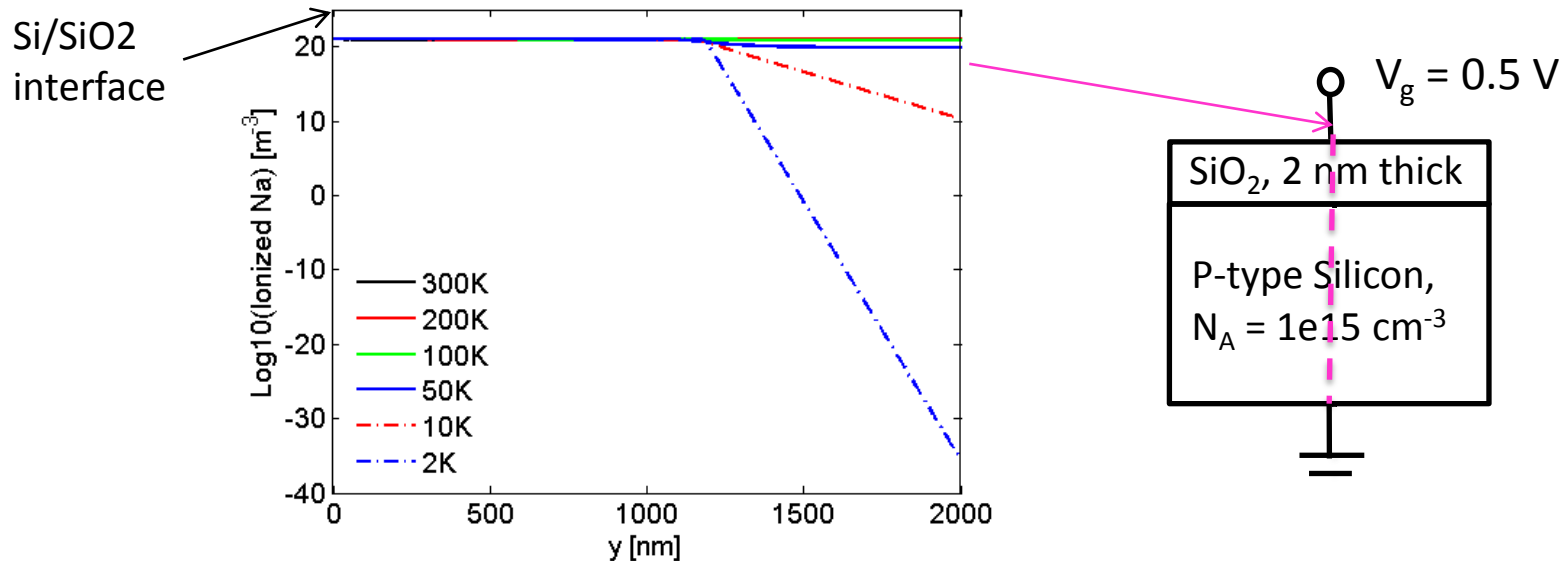
$$-\nabla(\epsilon_s \nabla \phi) = q(p - n + N_D^+ - N_A^-)$$

$$N_D^+ = \frac{N_D}{1 + 2 \exp\left(\frac{E_F - E_D}{k_B T}\right)}$$

$$N_A^- = \frac{N_A}{1 + 4 \exp\left(\frac{E_A - E_F}{k_B T}\right)}$$

Follow Fermi-Dirac distribution

$N_{A,D}$ = dopant concentration, $E_{A,D}$ = dopant activation energy level



Significant incomplete ionization for $T \leq 10 \text{ K}$

Poisson Solver – Boundary Condition

Three types of boundary conditions:

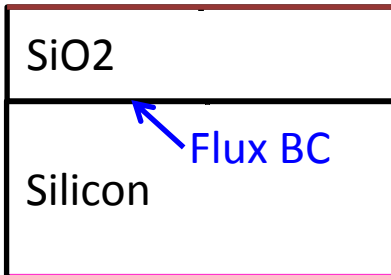
- Flux conservation b.t.w. different materials: $\varepsilon_{s1} \nabla \phi_1 \cdot \hat{\eta}_1 = \varepsilon_{s2} \nabla \phi_2 \cdot \hat{\eta}_2$
- Neumann condition: $\varepsilon_s \nabla \phi \cdot \hat{\eta} = 0$
- Dirichlet condition: $\phi = \text{const}$

Automatically satisfied in the finite element framework

Contact on insulator
Ohmic contact

Neumann BC

Contact on insulator



Ohmic contact

Neumann BC

Contact on insulator:

$$\phi_{ins} = V_g - (\Phi_M - q\phi_{ref}) / q$$

Ohmic contact:

charge neutrality and equilibrium conditions hold

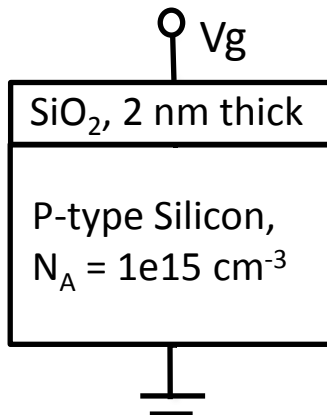
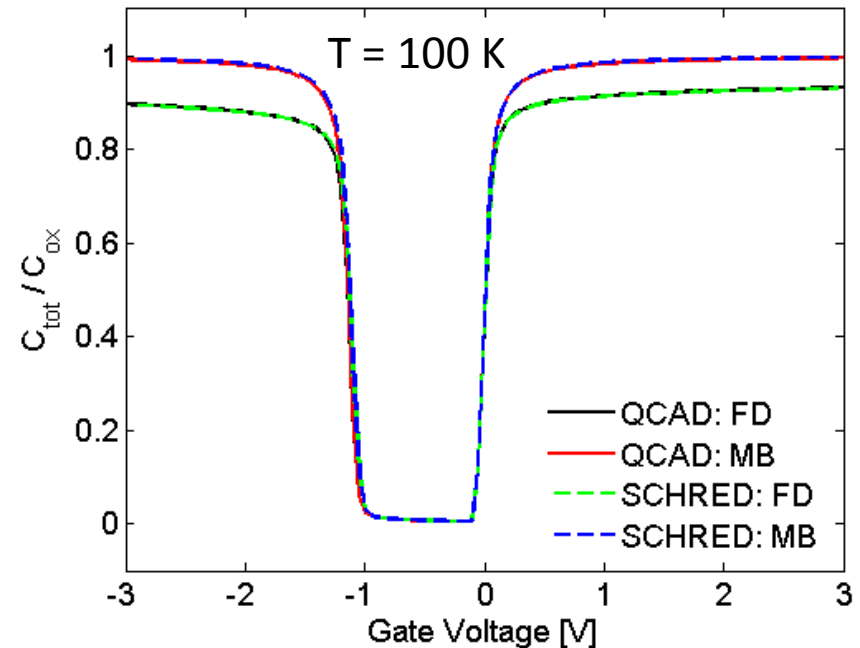
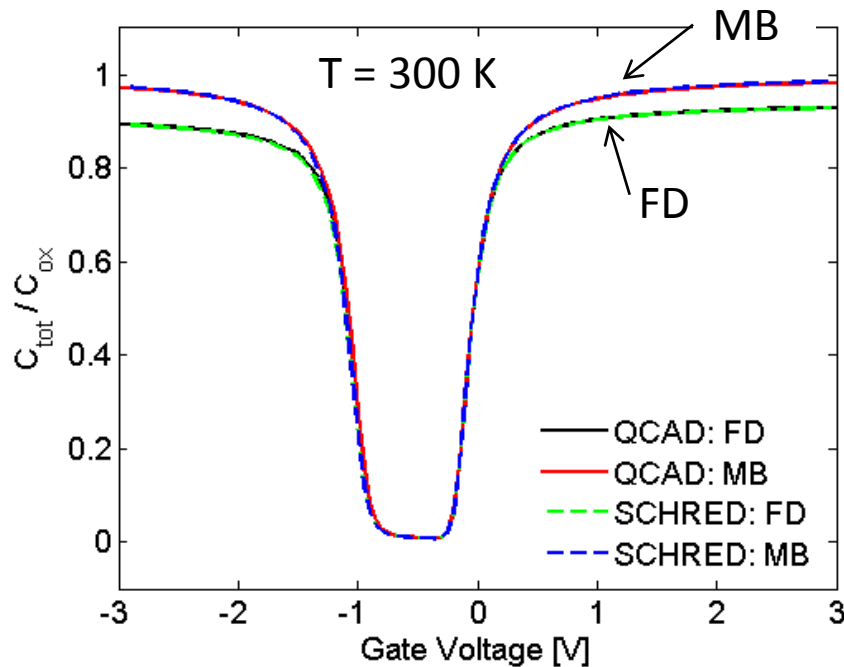
$$n(\phi) + N_A^-(\phi) = p(\phi) + N_D^+(\phi)$$

Example: p-type semiconductor with MB at 300 K,

$$\phi_{ohmic} = V_a - \frac{k_B T}{q} \ln \left(\frac{N_A}{n_i} \right)$$

Poisson Solver – Application 2D

Apply the Poisson solver to simulate a PMOS capacitor



The agreement between QCAD and SCHRED validates the accuracy of QCAD Poisson solver.

[2] <https://nanohub.org/tools/schred>

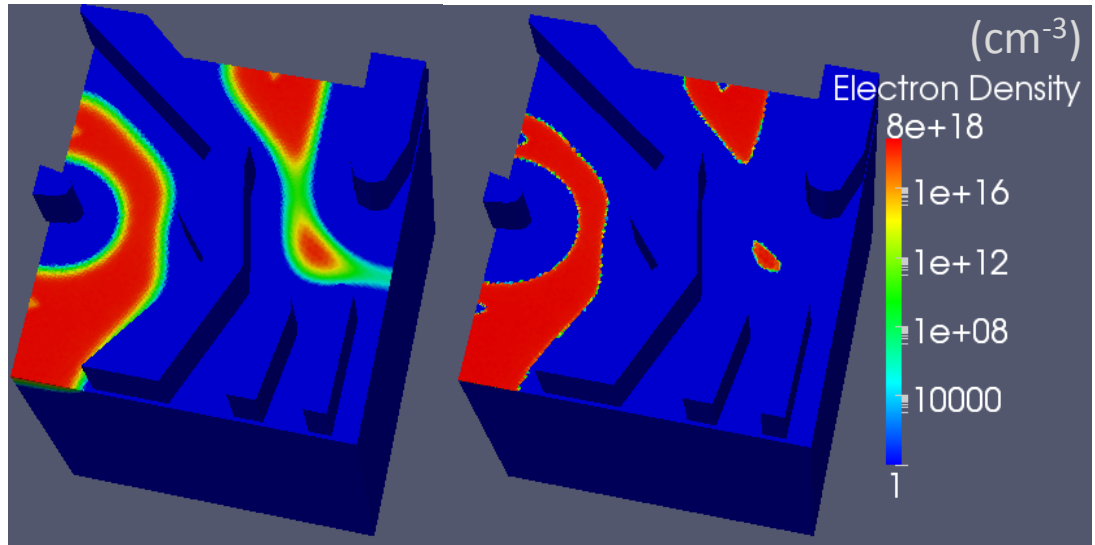
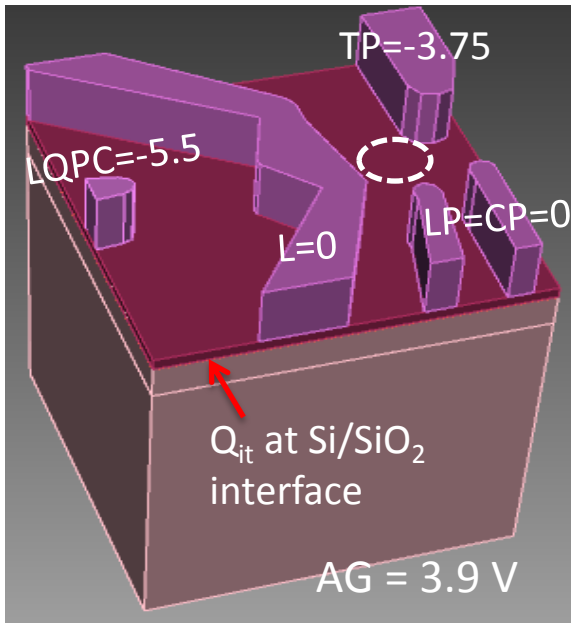
Poisson Solver – Application 3D

T = 50 K

$Q_{it} = -6.235 \times 10^{11} \text{ cm}^{-2}$

T = 2 K

$Q_{it} = -6.16 \times 10^{11} \text{ cm}^{-2}$



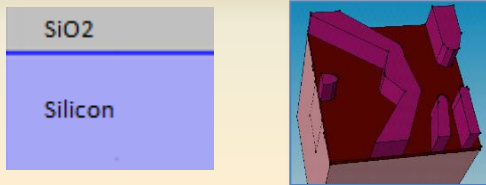
	Exp.	QCAD T = 50 K	QCAD T = 2 K	QCAD T = 2 K
$Q_{it} [\text{cm}^{-2}]$?	-6.235×10^{11}	-6.16×10^{11}	-6.235×10^{11}
# of e	1	1.009	0.997	0.21
AG [aF]	2.37	4.765	5.29	2.97
TP [aF]	0.48	0.315	0.35	0.18
CP [aF]	0.54	0.778	0.857	0.63
LP [aF]	0.29	0.582	0.642	0.52
L [aF]	0.56	1.91	2.11	1.30

Outline

Poisson Solver Background

$$-\nabla(\epsilon_s \nabla \phi) = q(p - n + N_D^+ - N_A^-)$$

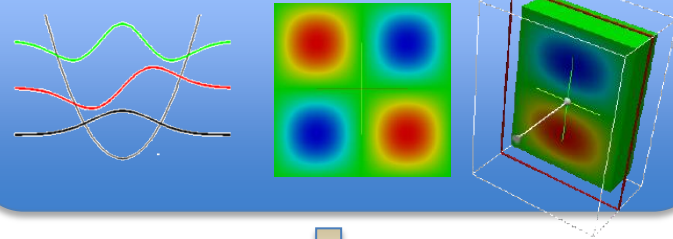
Applications of Poisson Solver



Schrodinger Solver

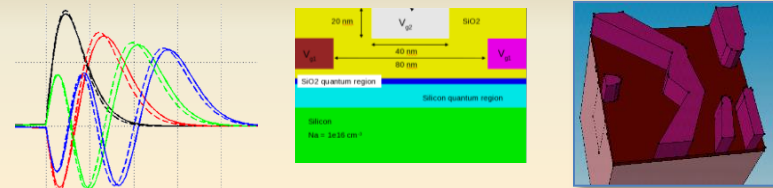
$$-\frac{\hbar^2}{2} \nabla \left(\frac{1}{m^*} \nabla \psi \right) + V\psi = E\psi$$

Applications of Schrodinger Solver



Self-Consistent Poisson-Schrodinger Solver

Applications of Self-Consistent P-S Solver



Schrodinger Solver

Time-independent effective mass Schrodinger equation:

$$-\frac{\hbar^2}{2} \nabla \left(\frac{1}{m^*} \nabla \psi(r) \right) + V(r) \psi(r) = E \psi(r)$$

Apply finite element method → Eigenvalue problem: $[H] [\psi] = [E] [\psi]$

→ Solved by Sandia high-performance eigensolver (Anasazi)

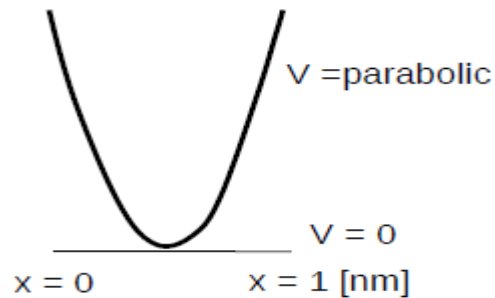
Three types of boundary conditions:

- Flux conservation b.t.w. different materials: $\frac{1}{m_1^*} \nabla \psi_1 \cdot \hat{\eta}_1 = \frac{1}{m_2^*} \nabla \psi_2 \cdot \hat{\eta}_2$
- Neumann condition: $\frac{1}{m^*} \nabla \psi \cdot \hat{\eta} = 0$
- Dirichlet condition: $\psi = 0$

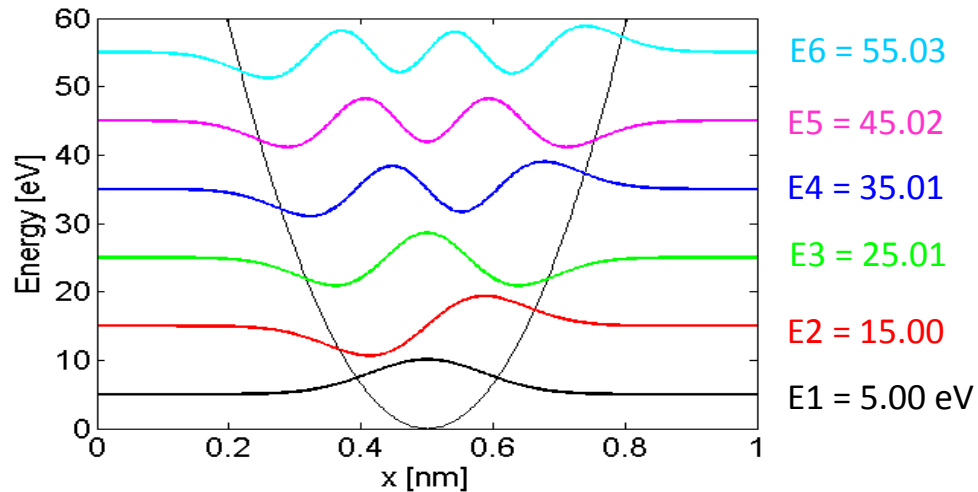
Automatically satisfied in the
finite element framework

Schrodinger Solver – Application 1D

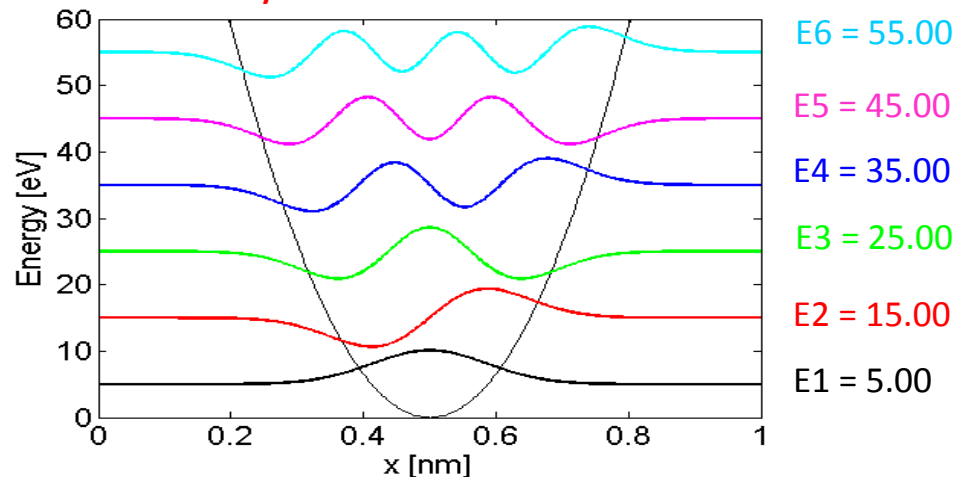
Apply the Schrodinger solver to a 1D parabolic potential well



QCAD wave functions



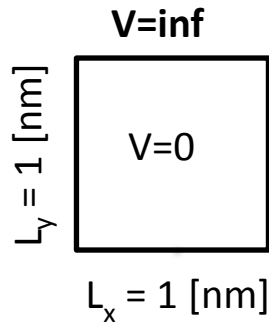
Analytic wave functions



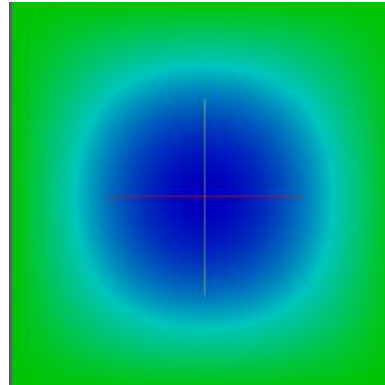
QCAD wave functions and energies agree well with analytic results.

Schrodinger Solver – Application 2D

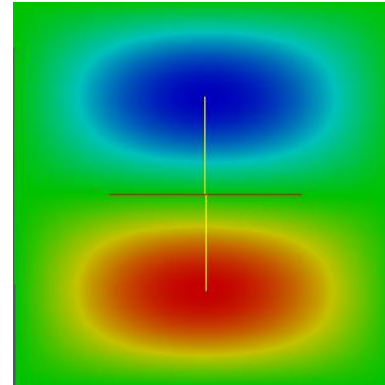
Apply the Schrodinger solver to a 2D square infinite potential well



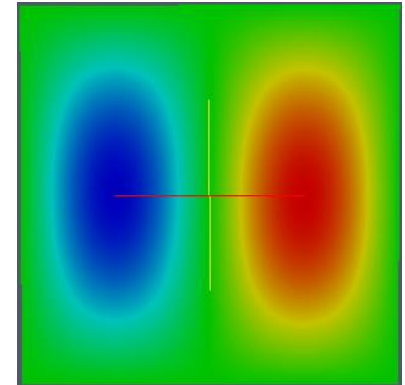
QCAD 1st WF



QCAD 2nd WF

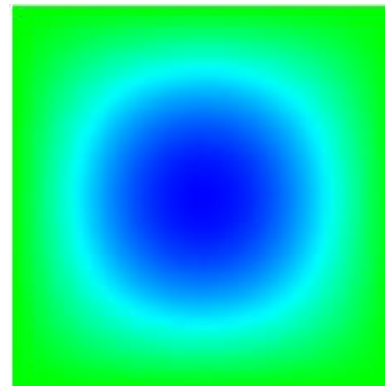


QCAD 3rd WF

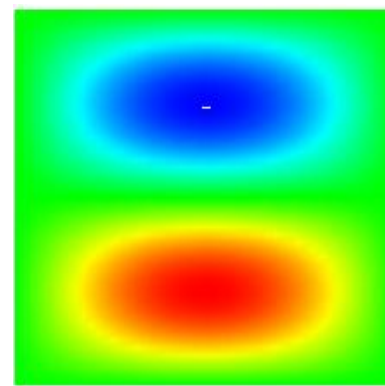


	QCAD	Analytic
E1 [eV]	0.7521	0.7521
E2 [eV]	1.8805	1.8802
E3 [eV]	1.8805	1.8802
E4 [eV]	3.0088	3.0084
E5 [eV]	3.7616	3.7605
E6 [eV]	3.7616	3.7605

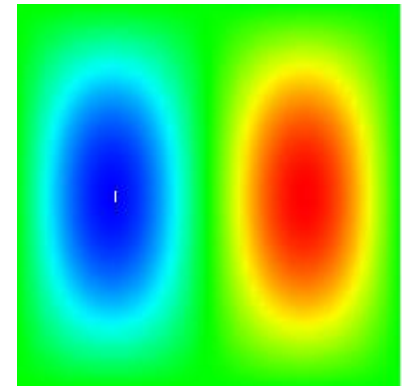
Analytic 1st WF



Analytic 2nd WF

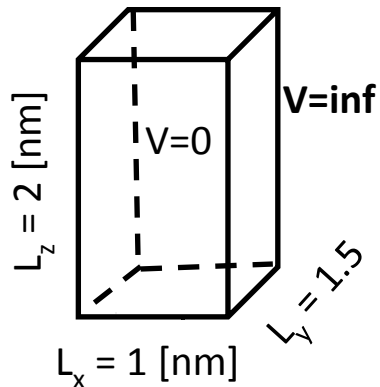


Analytic 3rd WF



Schrodinger Solver – Application 3D

Apply the Schrodinger solver to a 3D cube infinite potential well

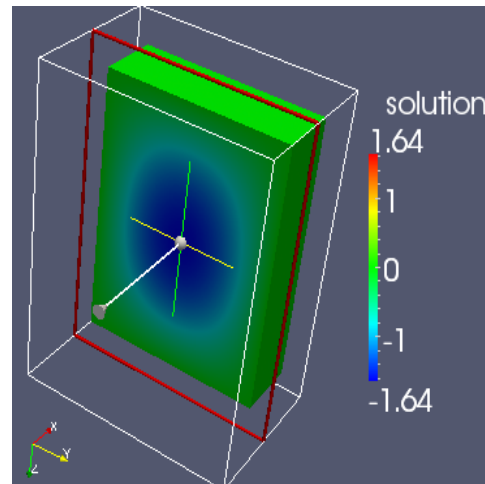


Analytic normalized WFs

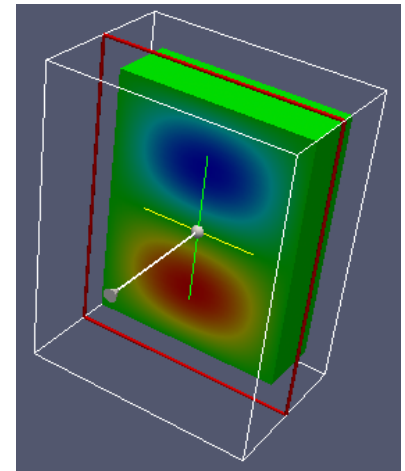
$$\psi(x, y, z) = \sqrt{\frac{8}{L_x L_y L_z}} \sin\left(\frac{\pi n_x x}{L_x}\right) \sin\left(\frac{\pi n_y y}{L_y}\right) \sin\left(\frac{\pi n_z z}{L_z}\right)$$

	QCAD	Analytic
E1 [eV]	0.6382	0.6373
E2 [eV]	0.9215	0.9194
E3 [eV]	1.1419	1.1387
E4 [eV]	1.3972	1.3895

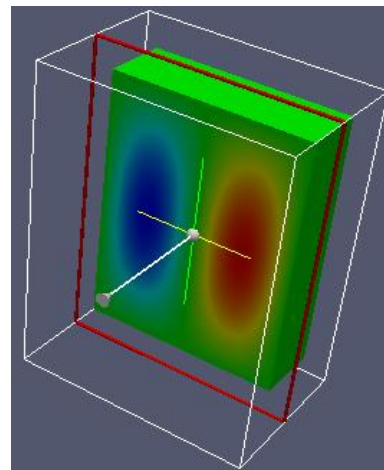
1st WF ($n_x=n_y=n_z=1$)



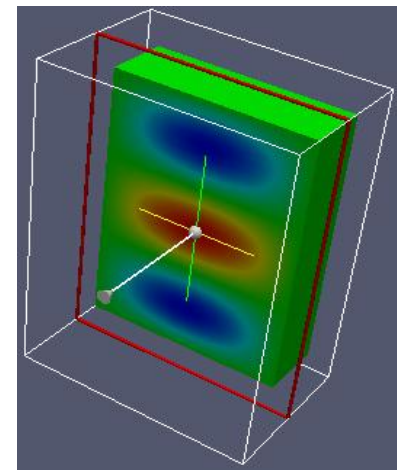
2nd WF ($n_x=n_y=1, n_z=2$)



3rd WF ($n_x=n_z=1, n_y=2$)



4th WF ($n_x=n_y=1, n_z=3$)

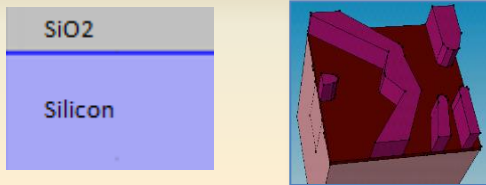


Outline

Poisson Solver Background

$$-\nabla(\epsilon_s \nabla \phi) = q(p - n + N_D^+ - N_A^-)$$

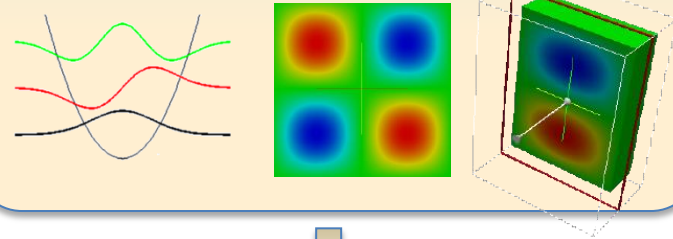
Applications of Poisson Solver



Schrodinger Solver

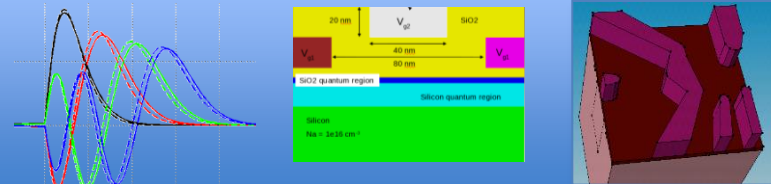
$$-\frac{\hbar^2}{2} \nabla \left(\frac{1}{m^*} \nabla \psi \right) + V\psi = E\psi$$

Applications of Schrodinger Solver



Self-Consistent Poisson-Schrodinger Solver

Applications of Self-Consistent P-S Solver



Self-Consistent Poisson-Schrodinger

Coupled Poisson equation: $-\nabla(\epsilon_s \nabla \phi) = q[p(\phi) + N_D^+(\phi) - N_A^-(\phi) - \underline{n(\phi, E_i, \psi_i)}]$

$$n(\phi, E_i, \psi_i) = \begin{cases} n(\phi) & \text{Semiclassical outside quantum region} \\ \sum_i N_i |\psi_i|^2 & \text{Quantum region} \end{cases}$$

1D (quantum well)

$$g_v \frac{m^* k_B T}{\pi \hbar^2} F_0(\eta_F)$$

2D (quantum wire)

$$g_v \left(\frac{2m^* k_B T}{\pi \hbar^2} \right)^{1/2} F_{-1/2}(\eta_F)$$

3D (quantum dot)

$$g_v \frac{2}{1 + \exp(-\eta_F)}$$

Where $\eta_F = \frac{E_F - E_i}{k_B T}$

$$F_k(\eta_F) = \frac{1}{\Gamma(k+1)} \int_0^\infty \frac{\epsilon^k d\epsilon}{1 + \exp(\epsilon - \eta_F)}$$

Fermi-Dirac integral of kth order

Coupled Schrodinger equation: $-\frac{\hbar^2}{2} \nabla \left(\frac{1}{m^*} \nabla \psi_i \right) + \underline{V(\phi, n)} \psi_i = E_i \psi_i$

$$q\phi_{ref} - \chi - q\phi + V_{xc}(n)$$

Parametrized in the Local

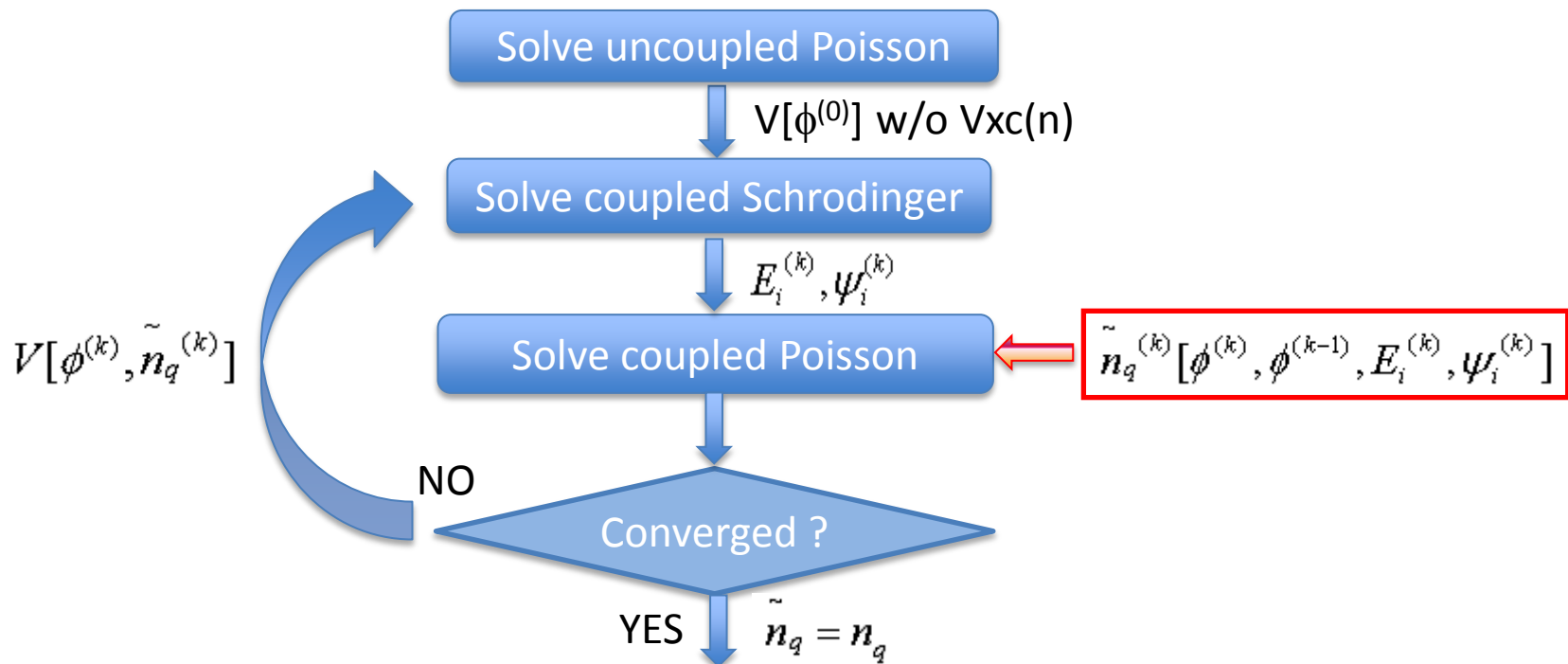
Density Approximation [3]

Self-Consistent Poisson-Schrodinger

Simple/Direct iteration of Poisson and Schrodinger leads to divergence due to strong coupling b.t.w. them.

Predictor-corrector iteration scheme [4] modifies quantum electron density calculation:

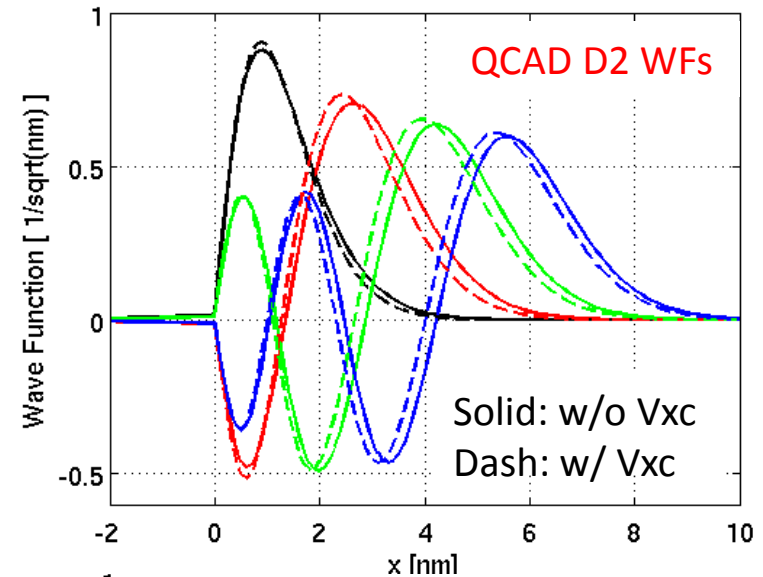
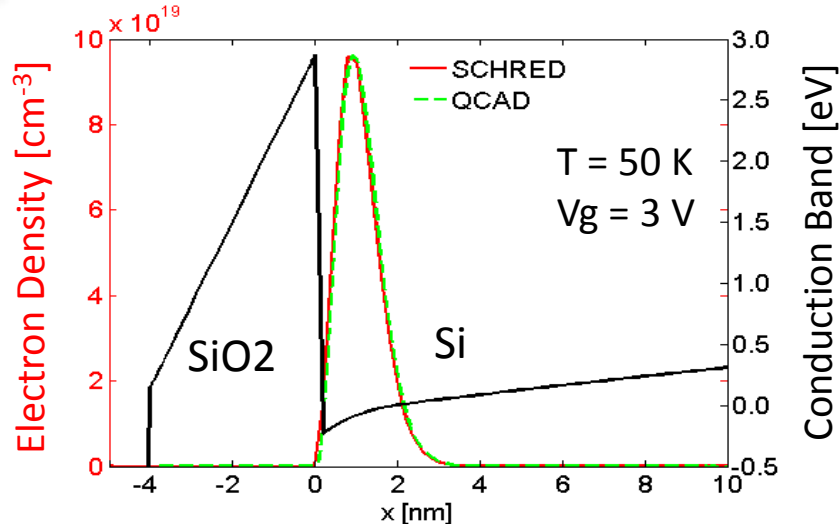
$$n_q(E_i, \psi_i) \text{ with } \eta_F = \frac{E_F - E_i}{k_B T} \Rightarrow \tilde{n}_q^{(k)}[\phi^{(k)}, \phi^{(k-1)}, E_i^{(k)}, \psi_i^{(k)}] \text{ with } \tilde{\eta}_F^{(k)} = \frac{E_F - E_i + q[\phi^{(k)} - \phi^{(k-1)}]}{k_B T}$$



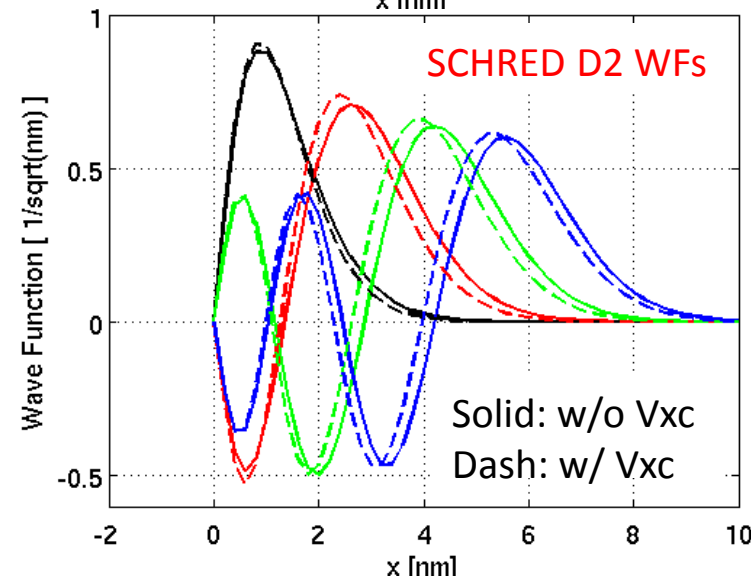
[4] A. Trellakis, A. T. Galick, A. Pacelli, and U. Ravaioli, J. Appl. Phys. **81**, 7880 (1997).

Self-Consistent P-S – Application 1D

Test structure: 1D MOS capacitor with $t_{ox} = 4$ nm, $N_a = 5e17$ cm⁻³



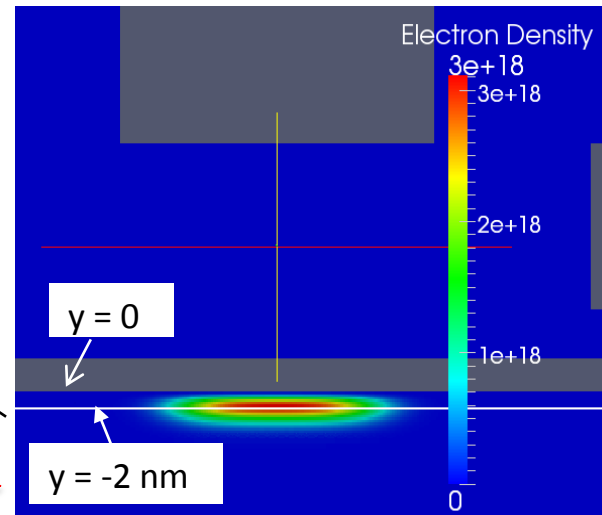
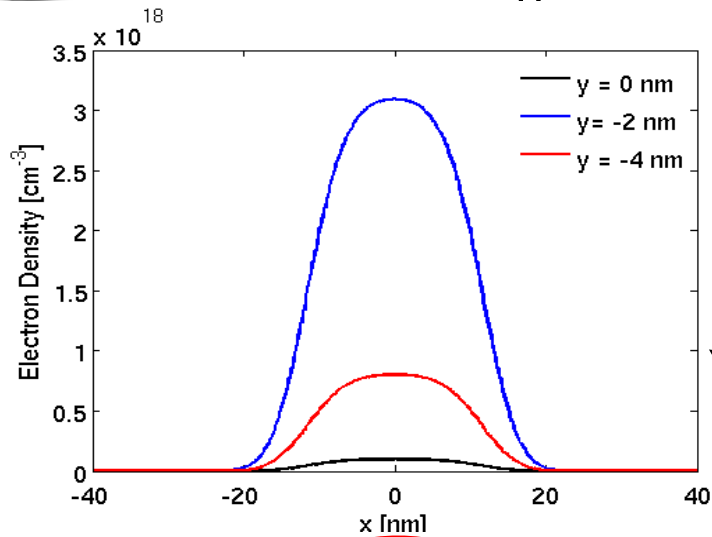
[meV]	SCHRED (w/o V_{xc})	QCAD (w/o V_{xc})	SCHRED (w/ V_{xc})	QCAD (w/ V_{xc})
E11	-71.76	-72.54	-73.68	-74.50
E12	26.12	26.71	45.63	45.72
E13	89.22	90.73	118.83	118.94
E14	142.27	144.69	175.60	176.10



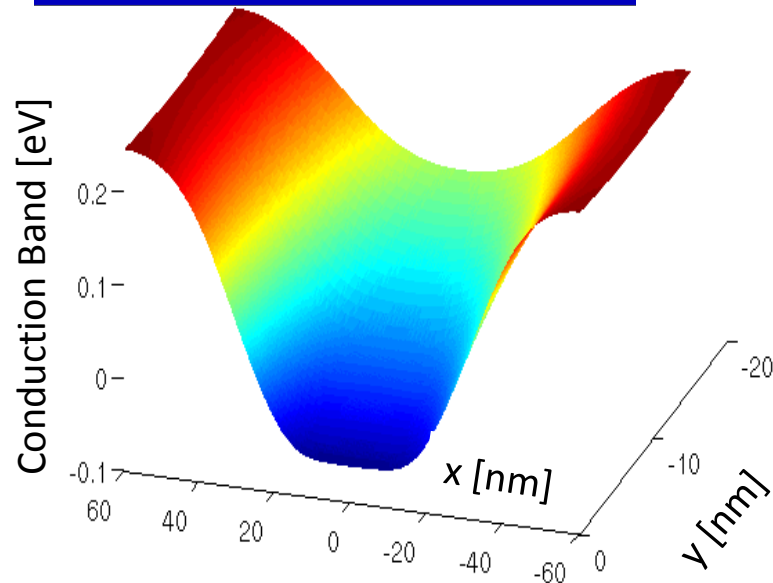
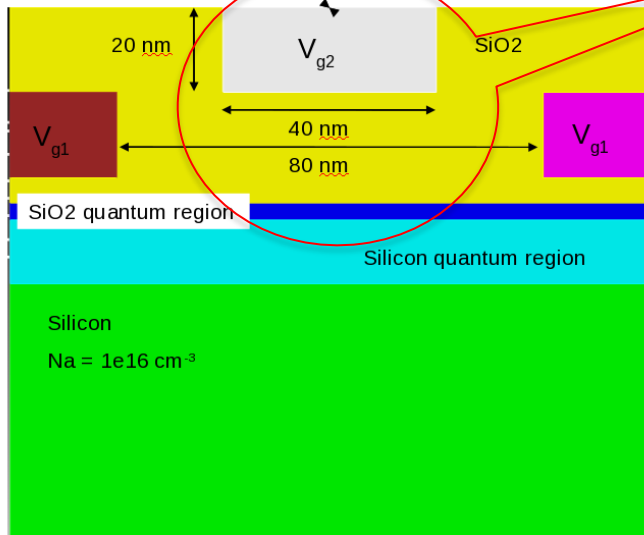
With V_{xc} , energy separation increases and wfs become more spatially confined.

Self-Consistent P-S – Application 2D

Test structure: gate-induced Silicon quantum wire from Ref. [5]

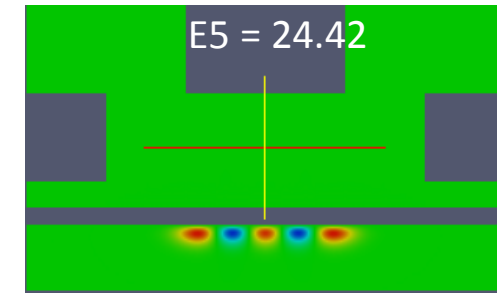
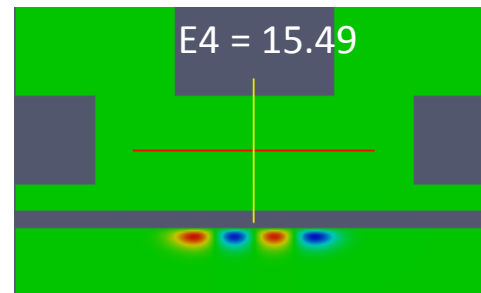
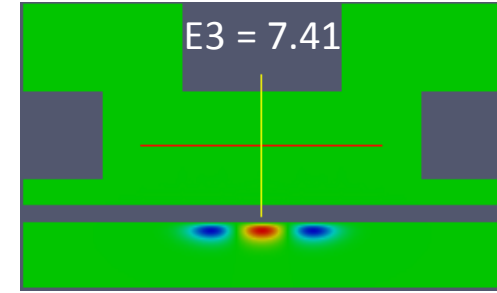
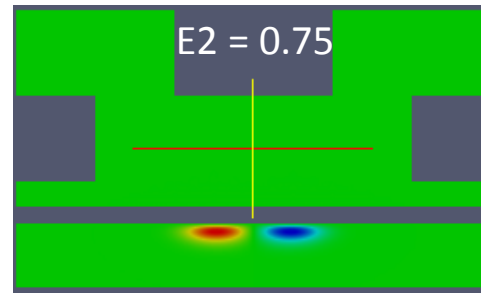
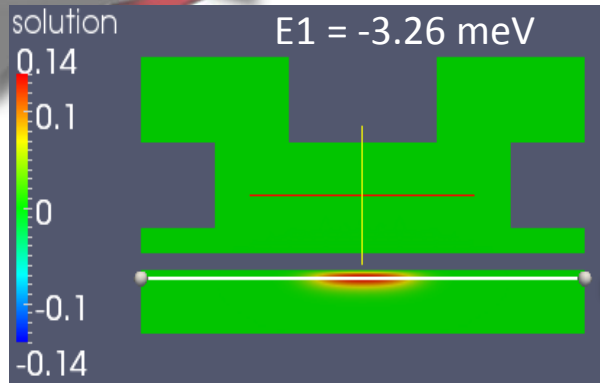


$T = 10$ K
 $V_{g1} = 0.8$ V
 $V_{g2} = 3.5$ V

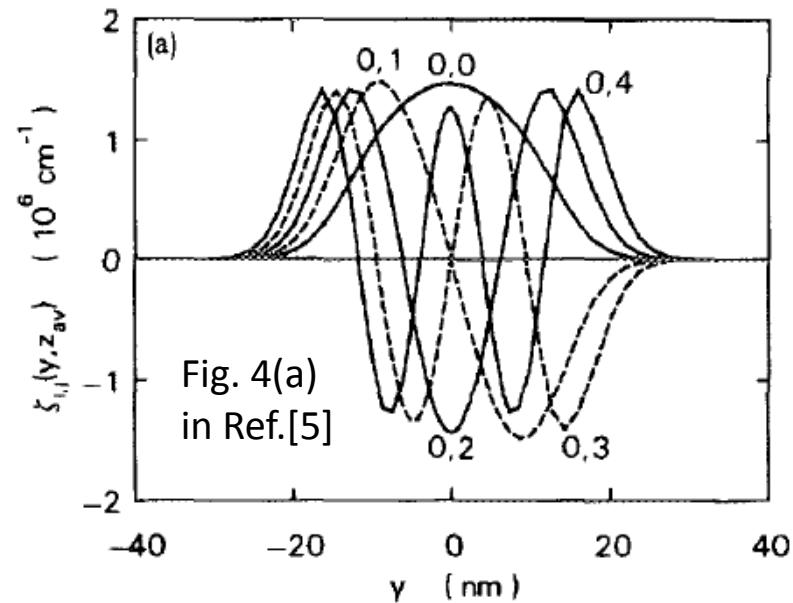
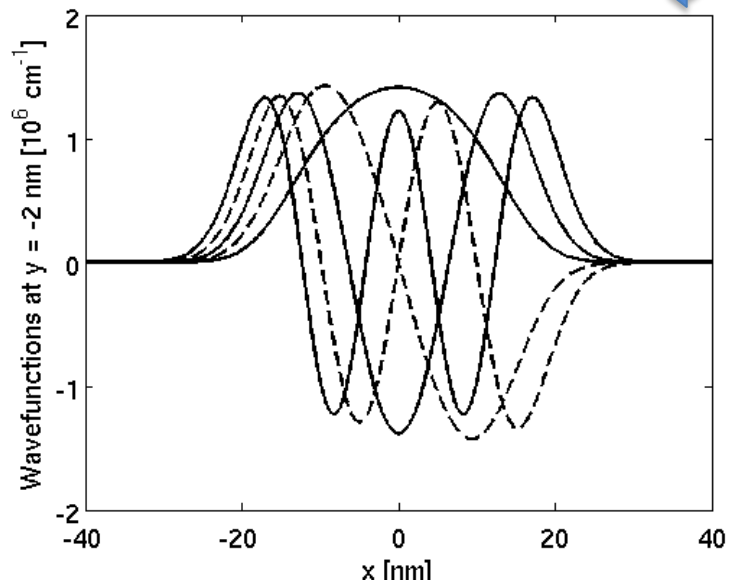


[5] Steven E. Laux and Frank Stern, Appl. Phys. Lett. **49**, 91 (1986).

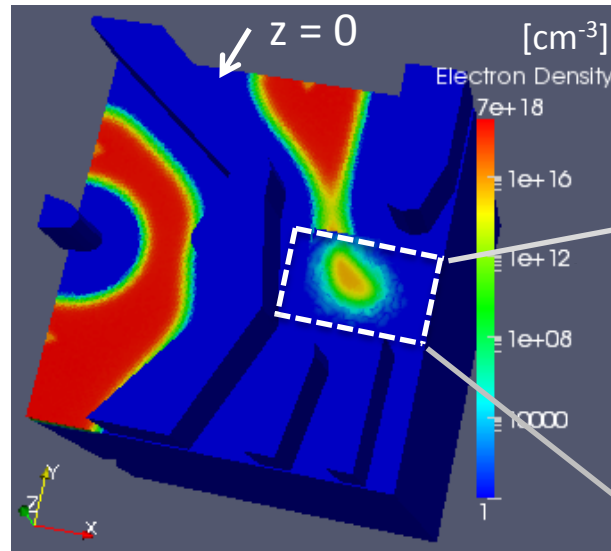
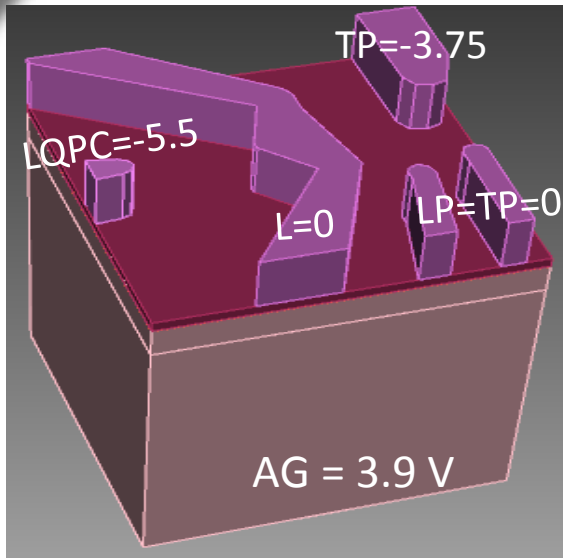
Self-Consistent P-S – Application 2D



QCAD Wfs at $y = -2 \text{ nm}$

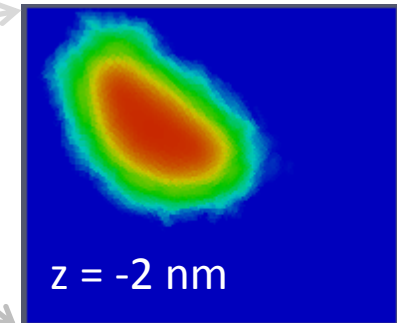


Self-Consistent P-S – Application 3D

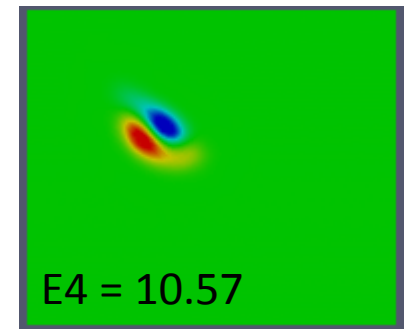
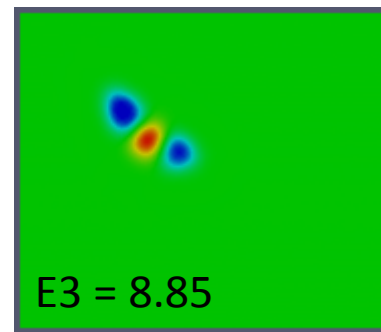
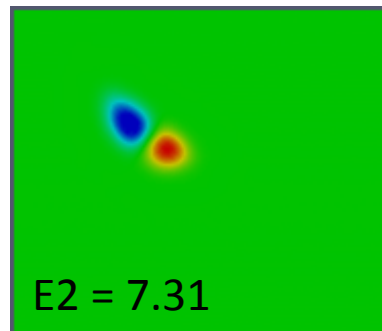
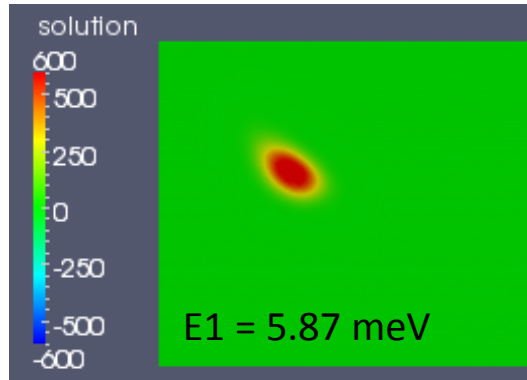


T = 50 K

$Q_{it} = -6 \times 10^{11} \text{ cm}^{-2}$



Lowest four wave functions at z = -2 nm surface

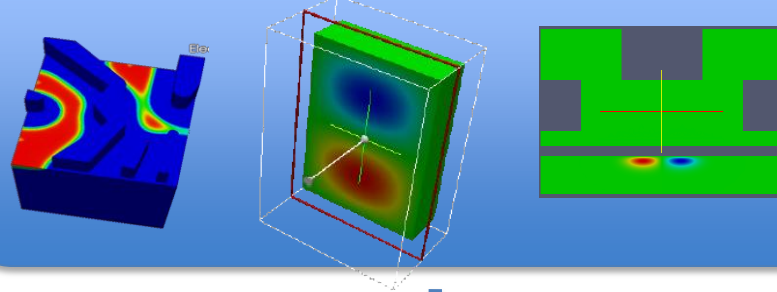


Conclusion

Discuss details of three QCAD solvers

$$\begin{aligned} -\nabla(\epsilon_s \nabla \phi) &= q(p - n + N_D^+ - N_A^-) \\ -\frac{\hbar^2}{2} \nabla \left(\frac{1}{m^*} \nabla \psi \right) + V\psi &= E\psi \\ n(\phi, E_i, \psi_i) &\leftrightarrow V(\phi, n) \end{aligned}$$

Demonstrate applications of QCAD solvers



Physics-based and robust QCAD tool for quantum devices modeling

Develop new capabilities

Simulate experimental quantum dots to provide feedback and design guidance for experiment